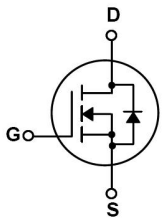
TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

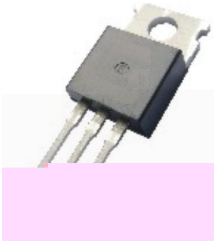
, ,

Low gate charge, low crss, fast switching.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

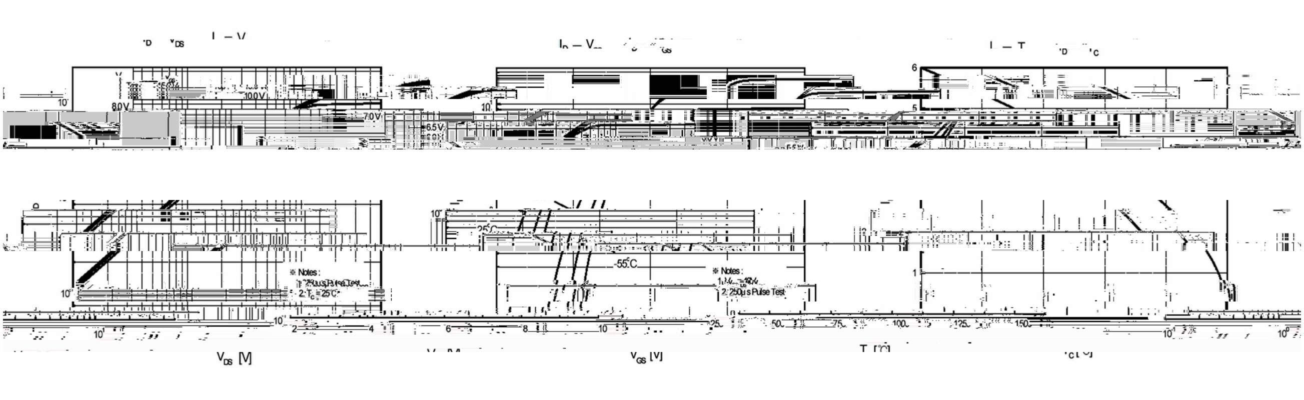


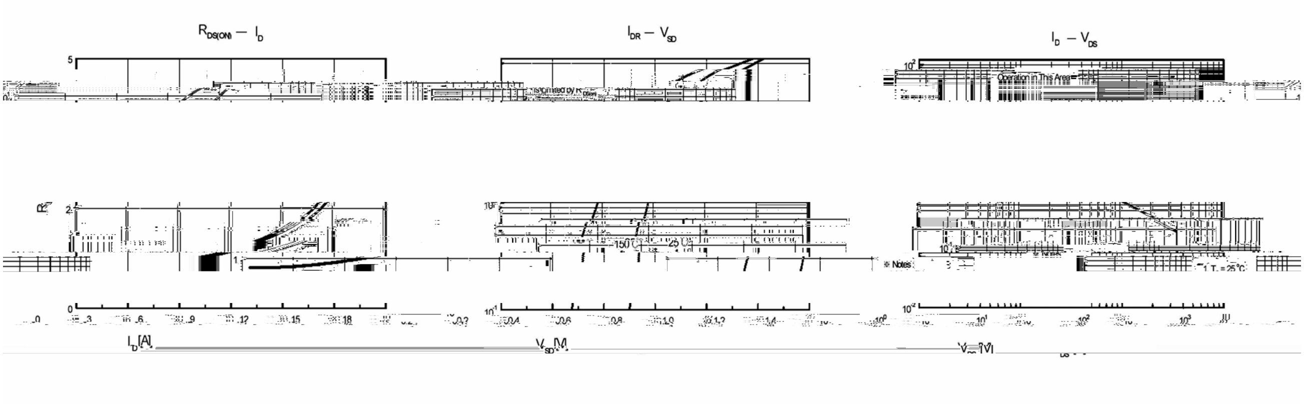


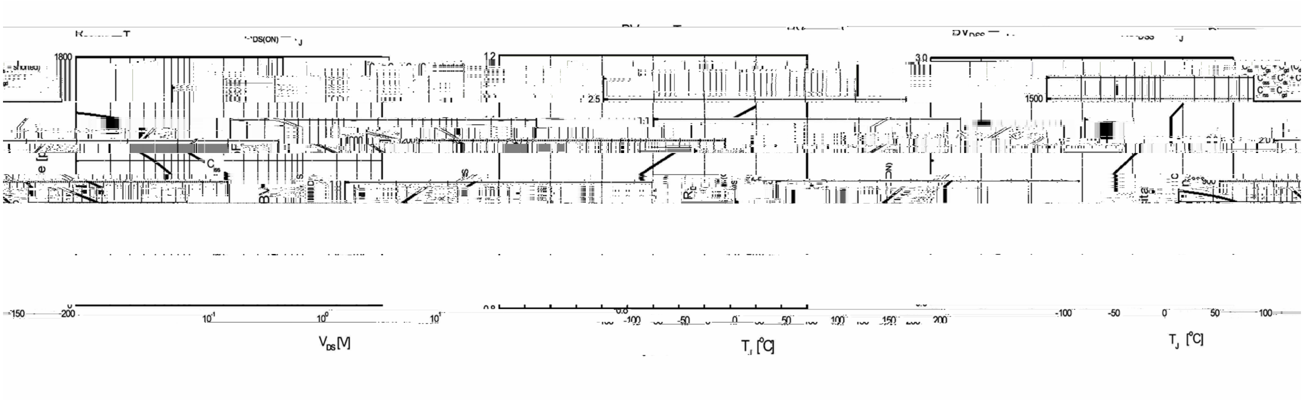
PIN1 G PIN 2 D PIN 3 S

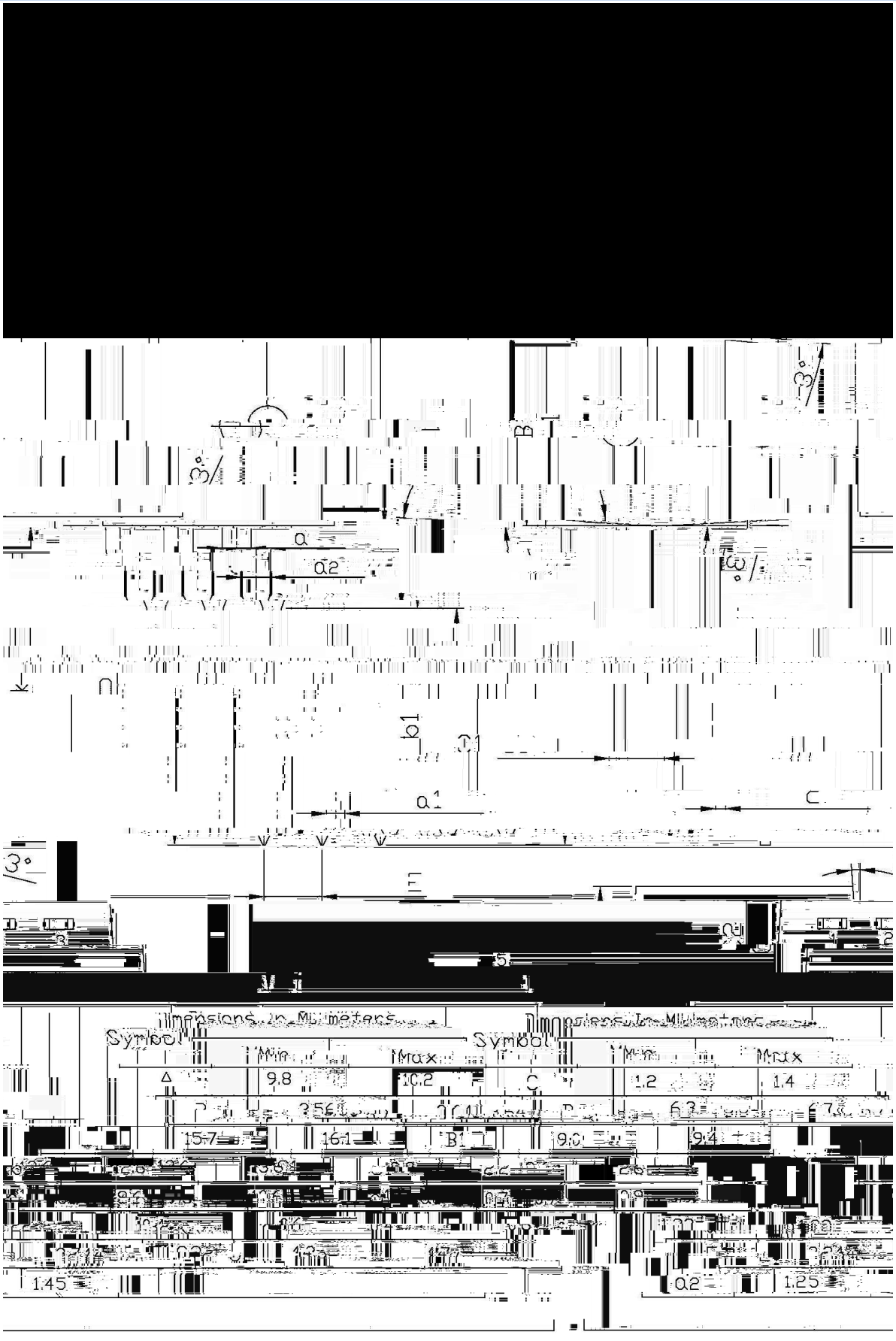
See Marking Instructions.

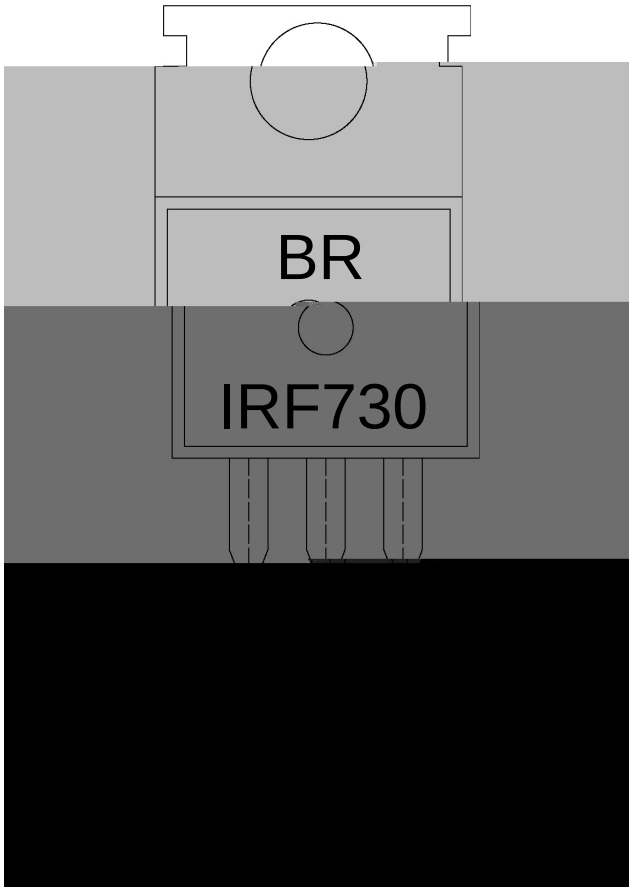
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	400	V
Drain Current	I_D(Tc=25)	6.0	A
	I_D(Tc=100)	3.6	A
Pulsed Drain Current	I_{DM}	24	A
Gate-Source Voltage	V_{GSS}	±30	V
Avalanche Current	I_{AR}	5.5	A
Single Pulsed Avalanche Energy	E_{AS}	390	mJ
Repetitive Avalanche Energy	E_{AR}	8.75	mJ
Total Power Dissipation	P_D(Tc=25)	87.5	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	




RDS(ON) — ID
IDR — VSD
ID — VDS




Dimensions In Millimeters
Symbol
Min
Max
9.8
10.2
15.7
16.1
9.0
9.4
1.45
1.25



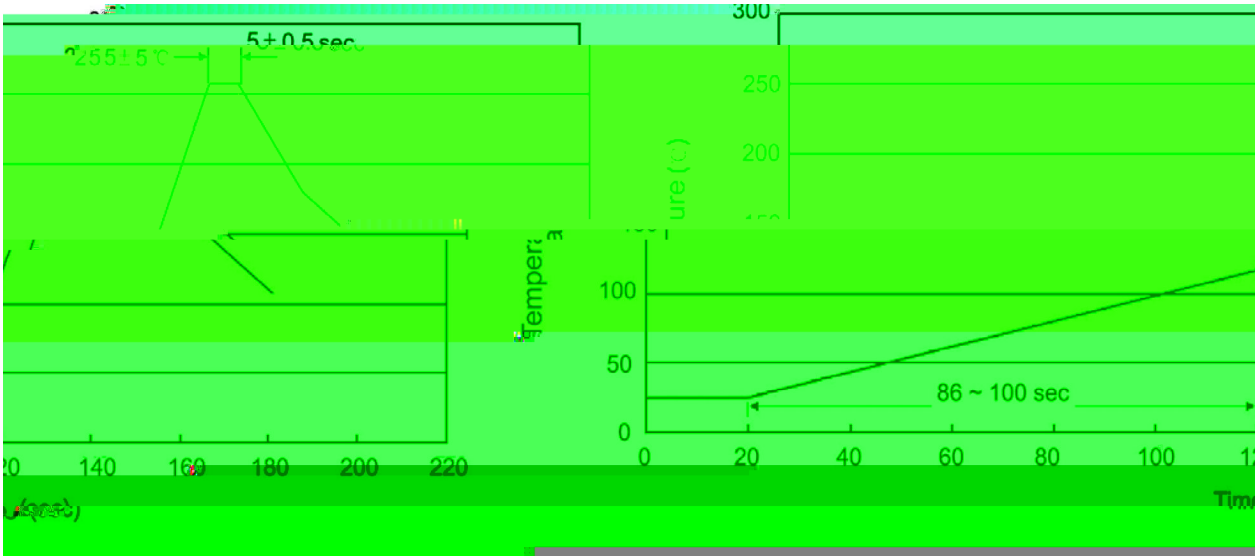
BR

IRF730

****

Note:

BR:	Company Code
IRF730:	Product Type.
****:	Lot No. Code, code change with Lot No.



						Note:	
1		25	150		60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5				5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3				2	10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ BULK

Package Type